#### CoolSET™-F2

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itevision mat	Jry. 2000-12-25	Datasheet
Previous Versi	on: 2.5.	
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4,17~22, 24~28, 30~31	Add ICE2A380P2	

Datasheet

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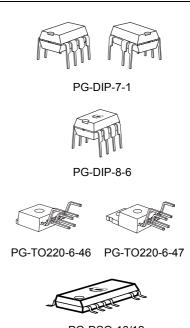


## CoolSET<sup>™</sup>-F2

# Off-Line SMPS Current Mode Controller with integrated 650V/800V CoolMOS™

## **Product Highlights**

- Best in class in DIP8, DIP7, TO220 and DSO16/12 packages
- No heat-sink required for DIP8, DIP7 and DSO16/12
- Increased creepage distance for TO220, DIP7 and DSO16/12
- Isolated drain for TO220 packages
- Lowest standby power dissipation
- Enhanced protection functions with Auto Restart Mode
- · Pb-free lead plating for all packages; RoHS compliant



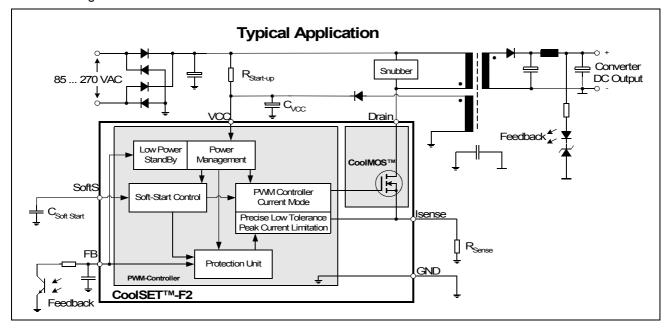
PG-DSO-16/12

## Features

- 650V/800V avalanche rugged CoolMOS™
- Only few external components required
- Input Vcc Undervoltage Lockout
- 67kHz/100kHz switching frequency
- Max duty cycle 72%
- Low Power Standby Mode to meet European Commission Requirements
- · Thermal Shut Down with Auto Restart
- Overload and Open Loop Protection
- Overvoltage Protection during Auto Restart
- Adjustable Peak Current Limitation via external resistor
- Overall tolerance of Current Limiting < ±5%</li>
- Internal Leading Edge Blanking
- User defined Soft Start
- Soft driving for low EMI

## Description

The second generation CoolSET<sup>™</sup>-F2 provides several special enhancements to satisfy the needs for low power standby and protection features. In standby mode frequency reduction is used to lower the power consumption and support a stable output voltage in this mode. The frequency reduction is limited to 20kHz/21.5 kHz to avoid audible noise. In case of failure modes like open loop, overvoltage or overload due to short circuit the device switches in Auto Restart Mode which is controlled by the internal protection unit. By means of the internal precise peak current limitation, the dimension of the transformer and the secondary diode can be sized lower which leads to more cost effective for the overall system.





## Overview

Туре	Package	V <sub>DS</sub>	Fosc	R <sub>DSon</sub> <sup>1)</sup>	230VAC ±15% <sup>2)</sup>	85-265 VAC <sup>2)</sup>
ICE2A0565	PG-DIP-8-6	650V	100kHz	4.7Ω	23W	13W
ICE2A165	PG-DIP-8-6	650V	100kHz	3.0Ω	31W	18W
ICE2A265	PG-DIP-8-6	650V	100kHz	0.9Ω	52W	32W
ICE2A365	PG-DIP-8-6	650V	100kHz	0.45Ω	67W	45W
ICE2B0565	PG-DIP-8-6	650V	67kHz	4.7Ω	23W	13W
ICE2B165	PG-DIP-8-6	650V	67kHz	3.0Ω	31W	18W
ICE2B265	PG-DIP-8-6	650V	67kHz	0.9Ω	52W	32W
ICE2B365	PG-DIP-8-6	650V	67kHz	0.45Ω	67W	45W
ICE2A0565Z	PG-DIP-7-1	650V	100kHz	4.7Ω	23W	13W
ICE2A180Z	PG-DIP-7-1	800V	100kHz	3.0Ω	29W	17W
ICE2A280Z	PG-DIP-7-1	800V	100KHz	0.8Ω	50W	31W

<sup>1)</sup> typ @ T=25°C

<sup>2)</sup> Maximum power rating at T<sub>a</sub>=75°C, T<sub>i</sub>=125°C and with copper area on PCB = 6cm<sup>2</sup>

Туре	Package	V <sub>DS</sub>	F <sub>osc</sub>	R <sub>DSon</sub> <sup>1)</sup>	230VAC ±15% <sup>2)</sup>	85-265 VAC <sup>2)</sup>
ICE2A0565G	PG-DSO-16/12	650V	100kHz	4.7Ω	23W	13W

<sup>1)</sup> typ @ T=25°C

<sup>2)</sup> Maximum power rating at  $T_a=75^{\circ}$ C,  $T_i=125^{\circ}$ C and with copper area on PCB = 6cm<sup>2</sup>

Туре	Package	V <sub>DS</sub>	Fosc	R <sub>DSon</sub> <sup>1)</sup>	230VAC ±15% <sup>2)</sup>	85-265 VAC <sup>2)</sup>
ICE2A765I	PG-TO-220-6-46	650V	100kHz	0.45Ω	240W	130W
ICE2B765I	PG-TO-220-6-46	650V	67kHz	0.45Ω	240W	130W
ICE2A765P2	PG-TO-220-6-47	650V	100kHz	0.45Ω	240W	130W
ICE2B765P2	PG-TO-220-6-47	650V	67kHz	0.45Ω	240W	130W
ICE2A380P2	PG-TO-220-6-47	800V	100kHz	1.89Ω	111W	60W

<sup>1)</sup> typ @ T=25°C

<sup>2)</sup> Maximum practical continuous power in an open frame design at  $T_a=75^{\circ}C$ ,  $T_j=125^{\circ}C$  and  $R_{thCA}=2.7$ K/W



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## **Pin Configuration and Functionality**

Pin Configuration with PG-DIP-7-1

#### **Pin Configuration and Functionality** 1

#### Pin Configuration with PG-DIP-8-6 1.1

Pin	Symbol	Function
1	SoftS	Soft-Start
2	FB	Feedback
3	Isense	Controller Current Sense Input, CoolMOS™ Source Output
4	Drain	650V <sup>1)</sup> /800V <sup>2)</sup> CoolMOS™ Drain
5	Drain	650V <sup>1)</sup> /800V <sup>2)</sup> CoolMOS™ Drain
6	N.C	Not connected
7	VCC	Controller Supply Voltage
8	GND	Controller Ground
1) . –		

Pin	Symbol	Function
1	SoftS	Soft-Start
2	FB	Feedback
3	Isense	Controller Current Sense Input, CoolMOS™ Source Output
4	N.C.	Not connected
5	Drain	650V <sup>1)</sup> /800V <sup>2)</sup> CoolMOS™ Drain
7	VCC	Controller Supply Voltage
8	GND	Controller Ground

1) at  $T_i = 110^{\circ}C$ 2)

at T<sub>i</sub> = 25°C

1.2

at T<sub>i</sub> = 110°C

2) at T<sub>i</sub> = 25°C

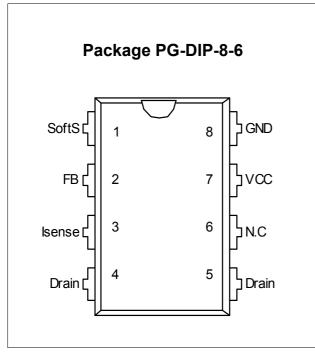
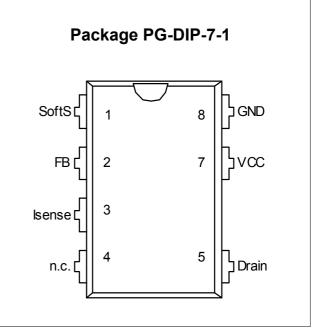
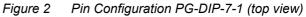


Figure 1 Pin Configuration PG-DIP-8-6 (top view)







## 1)



### 1.3 Pin Configuration with PG-TO220-6-46/ 7

Pin	Symbol	Function
1	Drain	650V <sup>1)</sup> CoolMOS™ Drain
3	Isense	Controller Current Sense Input, CoolMOS™ Source Output
4	GND	Controller Ground
5	VCC	Controller Supply Voltage
6	SoftS	Soft-Start
7	FB	Feedback

<sup>1)</sup> at T<sub>i</sub> = 110°C

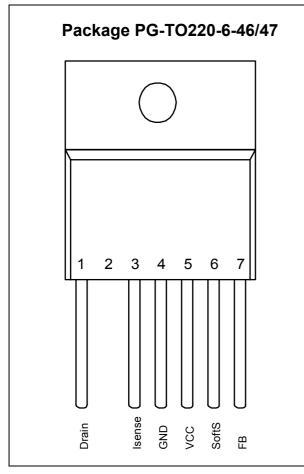


Figure 3 Pin Configuration PG-TO220-6-46/47 (top view)

## Pin Configuration and Functionality

### 1.4 Pin Configuration with PG-DSO-16/12

Pin	Symbol	Function				
1	N.C.	Not Connected				
2	SoftS	Soft-Start				
3	FB	Feedback				
4	Isense	Controller Current Sense Input, CoolMOS™ Source Output				
5	Drain	650V <sup>1)</sup> CoolMOS™ Drain				
6	Drain	650V <sup>1)</sup> CoolMOS™ Drain				
7	Drain	650V <sup>1)</sup> CoolMOS™ Drain				
8	Drain	650V <sup>1)</sup> CoolMOS™ Drain				
9	N.C.	Not Connected				
10	N.C.	Not Connected				
11	VCC	Controller Supply Voltage				
12	GND	Controller Ground				

<sup>1)</sup> at T<sub>j</sub> = 110°C

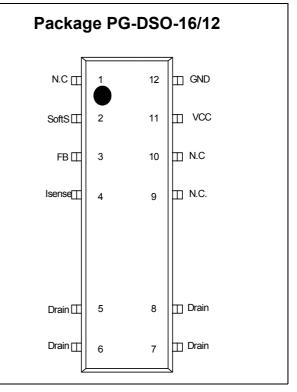


Figure 4 Pin Configuration PG-DSO-16/12 (top view)



## **Pin Configuration and Functionality**

#### 1.5 Pin Functionality

#### SoftS (Soft Start & Auto Restart Control)

This pin combines the function of Soft Start in case of Start Up and Auto Restart Mode and the controlling of the Auto Restart Mode in case of an error detection.

#### FB (Feedback)

The information about the regulation is provided by the FB Pin to the internal Protection Unit and to the internal PWM-Comparator to control the duty cycle.

#### Isense (Current Sense)

The Current Sense pin senses the voltage developed on the series resistor inserted in the source of the integrated CoolMOS<sup>TM</sup>. When Isense reaches the internal threshold of the Current Limit Comparator, the Driver output is disabled. By this means the Over Current Detection is realized.

Furthermore the current information is provided for the PWM-Comparator to realize the Current Mode.

#### Drain (Drain of integrated CoolMOS™)

Pin Drain is the connection to the Drain of the internal  $CoolMOS^{TM}$ .

#### VCC (Power supply)

This pin is the positive supply of the IC. The operating range is between 8.5V and 21V.

To provide overvoltage protection the driver gets disabled when the voltage becomes higher than 16.5V during Start Up Phase.

#### GND (Ground)

This pin is the ground of the primary side of the SMPS.



## Representative Blockdiagram

## 2 Representative Blockdiagram

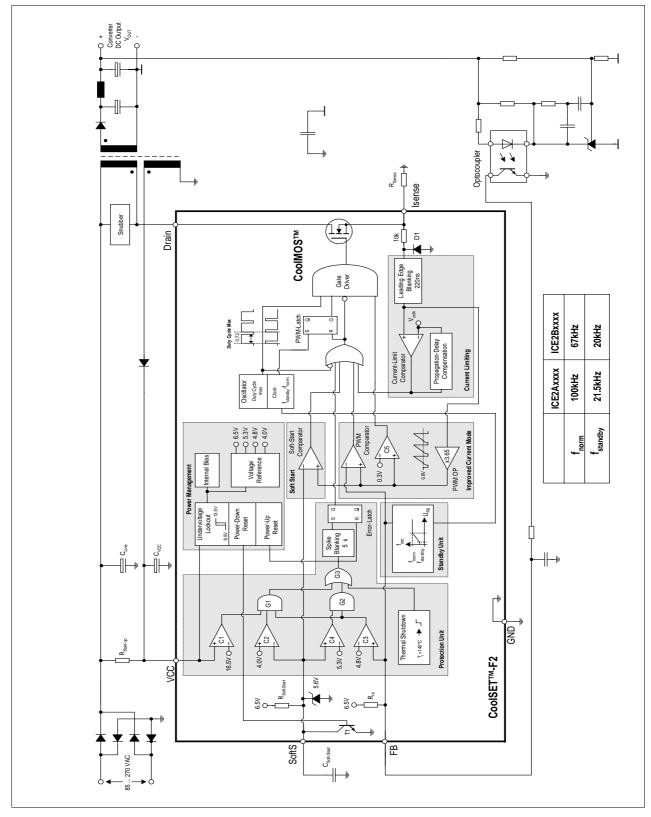


Figure 5 Representative Blockdiagram



## 3.1 Power Management

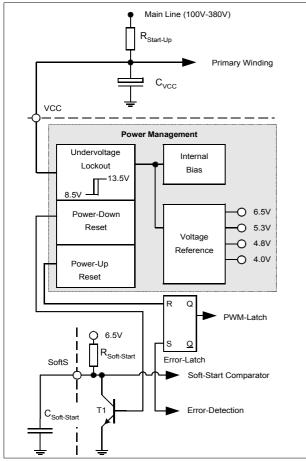


Figure 6 Power Management

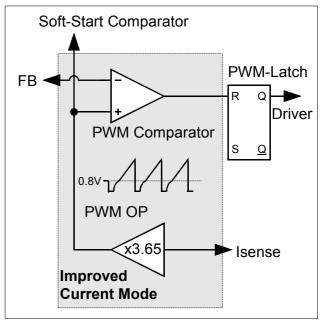
The Undervoltage Lockout monitors the external supply voltage V<sub>VCC</sub>. In case the IC is inactive the current consumption is max. 55µA. When the SMPS is plugged to the main line the current through R<sub>Start-up</sub> charges the external Capacitor C<sub>VCC</sub>. When V<sub>VCC</sub> exceeds the on-threshold V<sub>CCon</sub>=13.5V the internal bias circuit and the voltage reference are switched on. After that the internal bandgap generates a reference voltage V<sub>REF</sub>=6.5V to supply the internal circuits. To avoid uncontrolled ringing at switch-on a hysteresis is implemented which means that switch-off is only after active mode when Vcc falls below 8.5V.

In case of switch-on a Power Up Reset is done by resetting the internal error-latch in the protection unit.

When V<sub>VCC</sub> falls below the off-threshold V<sub>CCoff</sub>=8.5V the internal reference is switched off and the Power Down reset let T1 discharging the soft-start capacitor C<sub>Soft-Start</sub> at pin SoftS. Thus it is ensured that at every switch-on the voltage ramp at pin SoftS starts at zero.

## **Functional Description**

## 3.2 Improved Current Mode



#### Figure 7 Current Mode

Current Mode means that the duty cycle is controlled by the slope of the primary current. This is done by comparison the FB signal with the amplified current sense signal.

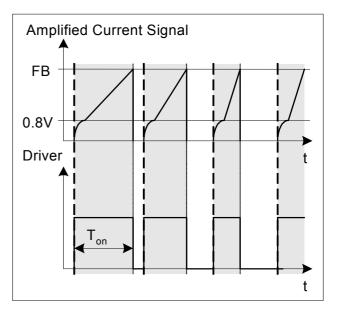


Figure 8 Pulse Width Modulation

In case the amplified current sense signal exceeds the FB signal the on-time  $T_{on}$  of the driver is finished by resetting the PWM-Latch (see Figure 8).

The primary current is sensed by the external series resistor  $R_{Sense}$  inserted in the source of the integrated CoolMOS<sup>TM</sup>. By means of Current Mode regulation, the



secondary output voltage is insensitive on line variations. Line variation changes the current waveform slope which controls the duty cycle.

The external  $R_{Sense}$  allows an individual adjustment of the maximum source current of the integrated CoolMOS<sup>TM</sup>.

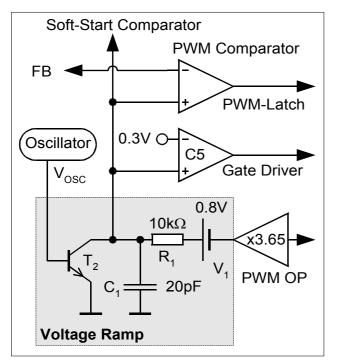


Figure 9 Improved Current Mode

To improve the Current Mode during light load conditions the amplified current ramp of the PWM-OP is superimposed on a voltage ramp, which is built by the switch  $T_2$ , the voltage source  $V_1$  and the 1st order low pass filter composed of  $R_1$  and  $C_1$ (see Figure 9, Figure 10). Every time the oscillator shuts down for max. duty cycle limitation the switch T2 is closed by  $V_{OSC}$ . When the oscillator triggers the Gate Driver T2 is opened so that the voltage ramp can start.

In case of light load the amplified current ramp is to small to ensure a stable regulation. In that case the Voltage Ramp is a well defined signal for the comparison with the FB-signal. The duty cycle is then controlled by the slope of the Voltage Ramp.

By means of the Comparator C5, the Gate Driver is switched-off until the voltage ramp exceeds 0.3V. It allows the duty cycle to be reduced continuously till 0% by decreasing  $V_{FB}$  below that threshold.

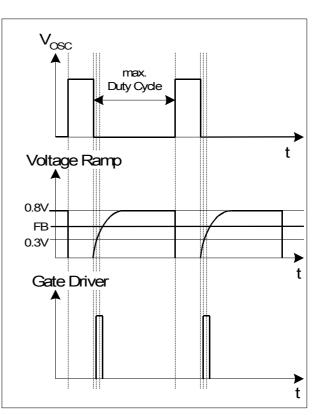


Figure 10 Light Load Conditions

## 3.2.1 PWM-OP

The input of the PWM-OP is applied over the internal leading edge blanking to the external sense resistor  $R_{Sense}$  connected to pin Isense.  $R_{Sense}$  converts the source current into a sense voltage. The sense voltage is amplified with a gain of 3.65 by PWM OP. The output of the PWM-OP is connected to the voltage source V1. The voltage ramp with the superimposed amplified current signal is fed into the positive inputs of the PWM-Comparator, C5 and the Soft-Start-Comparator.

#### 3.2.2 PWM-Comparator

The PWM-Comparator compares the sensed current signal of the integrated CoolMOS<sup>TM</sup> with the feedback signal V<sub>FB</sub> (see Figure 11). V<sub>FB</sub> is created by an external optocoupler or external transistor in combination with the internal pull-up resistor R<sub>FB</sub> and provides the load information of the feedback circuitry. When the amplified current signal of the integrated CoolMOS<sup>TM</sup> exceeds the signal V<sub>FB</sub> the PWM-Comparator switches off the Gate Driver.



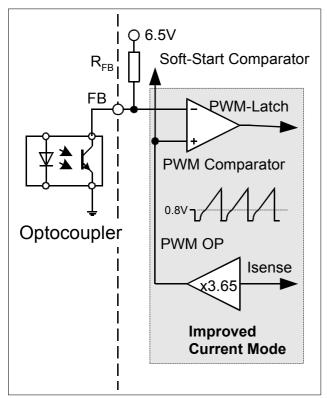


Figure 11 PWM Controlling

## 3.3 Soft-Start

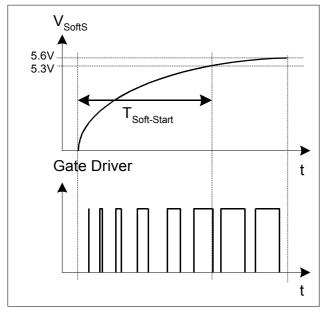


Figure 12 Soft-Start Phase

The Soft-Start is realized by the internal pull-up resistor  $R_{Soft-Start}$  and the external Capacitor  $C_{Soft-Start}$  (see Figure 5). The Soft-Start voltage  $V_{SoftS}$  is generated by charging the external capacitor  $C_{Soft-Start}$  by the internal

## **Functional Description**

pull-up resistor  $\mathsf{R}_{\mathsf{Soft-Start}}.$  The Soft-Start-Comparator compares the voltage at pin SoftS at the negative input with the ramp signal of the PWM-OP at the positive input. When Soft-Start voltage  $V_{\text{SoftS}}$  is less than Feedback voltage V<sub>FB</sub> the Soft-Start-Comparator limits the pulse width by resetting the PWM-Latch (see Figure 12). In addition to Start-Up, Soft-Start is also activated at each restart attempt during Auto Restart. By means of the above mentioned  $C_{\text{Soft-Start}}$  the Soft-Start can be defined by the user. The Soft-Start is finished when  $V_{\text{SoftS}}$  exceeds 5.3V. At that time the Protection Unit is activated by Comparator C4 and senses the FB by Comparator C3 wether the voltage is below 4.8V which means that the voltage on the secondary side of the SMPS is settled. The internal Zener Diode at SoftS has a clamp voltage of 5.6V to prevent the internal circuit from saturation (see Figure 13).

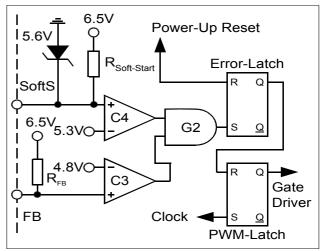


Figure 13 Activation of Protection Unit

The Start-Up time  $T_{Start-Up}$  within the converter output voltage  $V_{OUT}$  is settled must be shorter than the Soft-Start Phase  $T_{Soft-Start}$  (see Figure 14).

$$C_{Soft-Start} = \frac{T_{Soft-Start}}{R_{Soft-Start} \times 1.69}$$

By means of Soft-Start there is an effective minimization of current and voltage stresses on the integrated CoolMOS<sup>™</sup>, the clamp circuit and the output overshoot and prevents saturation of the transformer during Start-Up.



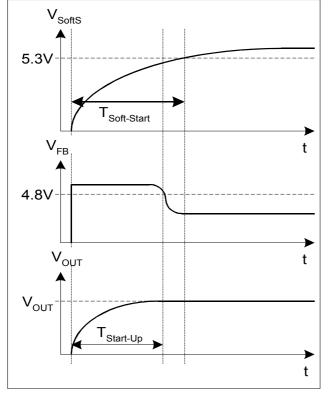


Figure 14 Start Up Phase

### 3.4 Oscillator and Frequency Reduction

#### 3.4.1 Oscillator

The oscillator generates a frequency  $f_{switch} = 67 kHz/100 kHz$ . A resistor, a capacitor and a current source and current sink which determine the frequency are integrated. The charging and discharging current of the implemented oscillator capacitor are internally trimmed, in order to achieve a very accurate switching frequency. The ratio of controlled charge to discharge current is adjusted to reach a max. duty cycle limitation of D<sub>max</sub>=0.72.

## 3.4.2 Frequency Reduction

The frequency of the oscillator is depending on the voltage at pin FB. The dependence is shown in Figure 15. This feature allows a power supply to operate at lower frequency at light loads thus lowering the switching losses while maintaining good cross regulation performance and low output ripple. In case of low power the power consumption of the whole SMPS can now be reduced very effective. The minimal reachable frequency is limited to 20kHz/21.5 kHz to avoid audible noise in any case.

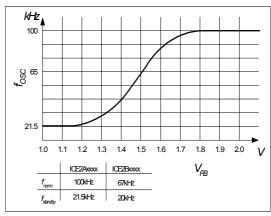


Figure 15 Frequency Dependence

## 3.5 Current Limiting

There is a cycle by cycle current limiting realized by the Current-Limit Comparator to provide an overcurrent detection. The source current of the integrated CoolMOS<sup>TM</sup> is sensed via an external sense resistor  $R_{Sense}$ . By means of  $R_{Sense}$  the source current is transformed to a sense voltage  $V_{Sense}$ . When the voltage  $V_{Sense}$  exceeds the internal threshold voltage  $V_{csth}$  the Current-Limit-Comparator immediately turns off the gate drive. To prevent the Current Limiting from distortions caused by leading edge spikes a Leading Edge Blanking is integrated at the Current Sense. Furthermore a Propagation Delay Compensation is added to support the immediate shut down of the CoolMOS<sup>TM</sup> in case of overcurrent.

## 3.5.1 Leading Edge Blanking

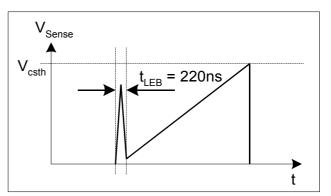


Figure 16 Leading Edge Blanking

Each time when CoolMOS<sup>TM</sup> is switched on a leading spike is generated due to the primary-side capacitances and secondary-side rectifier reverse recovery time. To avoid a premature termination of the switching pulse this spike is blanked out with a time constant of  $t_{LEB}$  = 220ns. During that time the output of





the Current-Limit Comparator cannot switch off the gate drive.

#### 3.5.2 Propagation Delay Compensation

In case of overcurrent detection by  $I_{\text{Limit}}$  the shut down of CoolMOS<sup>TM</sup> is delayed due to the propagation delay of the circuit. This delay causes an overshoot of the peak current  $I_{\text{peak}}$  which depends on the ratio of dl/dt of the peak current (see Figure 17).

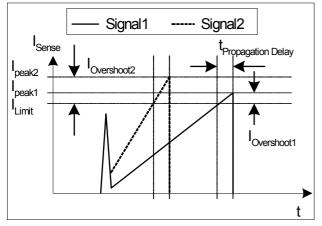
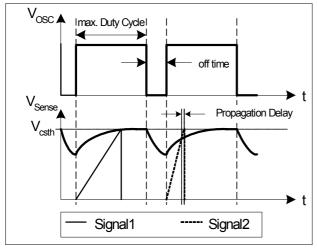


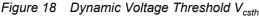
Figure 17 Current Limiting

The overshoot of Signal2 is bigger than of Signal1 due to the steeper rising waveform.

A propagation delay compensation is integrated to bound the overshoot dependent on dl/dt of the rising primary current. That means the propagation delay time between exceeding the current sense threshold  $V_{csth}$  and the switch off of CoolMOS<sup>TM</sup> is compensated over temperature within a range of at least.

$$0 \le R_{Sense} \times \frac{dI_{peak}}{dt} \le \frac{dV_{Sense}}{dt}$$





The propagation delay compensation is done by means of a dynamic threshold voltage  $V_{csth}$  (see Figure 18). In case of a steeper slope the switch off of the driver is earlier to compensate the delay.

E.g.  $I_{peak} = 0.5A$  with  $R_{Sense} = 2$ . Without propagation delay compensation the current sense threshold is set to a static voltage level  $V_{csth}$ =1V. A current ramp of dl/dt = 0.4A/µs, that means  $dV_{Sense}/dt = 0.8V/µs$ , and a propagation delay time of i.e.  $t_{Propagation \ Delay}$ =180ns leads then to a  $I_{peak}$  overshoot of 14.4%. By means of propagation delay compensation the overshoot is only

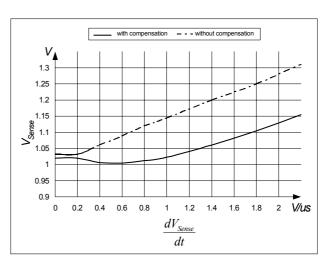


Figure 19 Overcurrent Shutdown

#### 3.6 PWM-Latch

about 2% (see Figure 19).

The oscillator clock output applies a set pulse to the PWM-Latch when initiating CoolMOS<sup>™</sup> conduction. After setting the PWM-Latch can be reset by the PWM-OP, the Soft-Start-Comparator, the Current-Limit-Comparator, Comparator C3 or the Error-Latch of the Protection Unit. In case of resetting the driver is shut down immediately.

#### 3.7 Driver

The driver-stage drives the gate of the CoolMOS<sup>TM</sup> and is optimized to minimize EMI and to provide high circuit efficiency. This is done by reducing the switch on slope when reaching the CoolMOS<sup>TM</sup> threshold. This is achieved by a slope control of the rising edge at the driver's output (see Figure 20) to the CoolMOS<sup>TM</sup> gate. Thus the leading switch on spike is minimized. When CoolMOS<sup>TM</sup> is switched off, the falling shape of the driver is slowed down when reaching 2V to prevent an overshoot below ground. Furthermore the driver circuit is designed to eliminate cross conduction of the output stage. At voltages below the undervoltage lockout threshold V<sub>VCCoff</sub> the gate drive is active low.



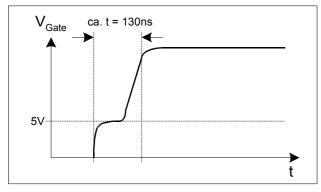


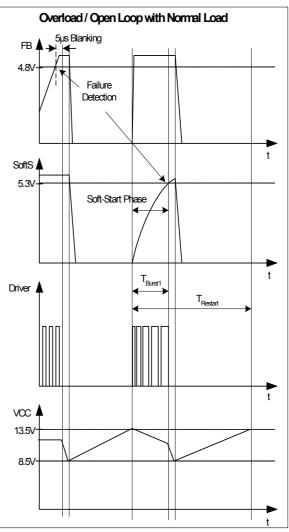
Figure 20 Internal Gate Rising Slope

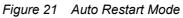
## 3.8 **Protection Unit (Auto Restart Mode)**

An overload, open loop and overvoltage detection is integrated within the Protection Unit. These three failure modes are latched by an Error-Latch. Additional thermal shutdown is latched by the Error-Latch. In case of those failure modes the Error-Latch is set after a blanking time of 5µs and the CoolMOS<sup>™</sup> is shut down. That blanking prevents the Error-Latch from distortions caused by spikes during operation mode.

## 3.8.1 Overload / Open Loop with Normal Load

Figure 21 shows the Auto Restart Mode in case of overload or open loop with normal load. The detection of open loop or overload is provided by the Comparator C3, C4 and the AND-gate G2 (see Figure 22). The detection is activated by C4 when the voltage at pin SoftS exceeds 5.3V. Till this time the IC operates in the Soft-Start Phase. After this phase the comparator C3 can set the Error-Latch in case of open loop or overload which leads the feedback voltage  $V_{\mbox{\scriptsize FB}}$  to exceed the threshold of 4.8V. After latching VCC decreases till 8.5V and inactivates the IC. At this time the external Soft-Start capacitor is discharged by the internal transistor T1 due to Power Down Reset. When the IC is inactive V<sub>VCC</sub> increases till V<sub>CCon</sub> = 13.5V by charging the Capacitor C<sub>VCC</sub> by means of the Start-Up Resistor R<sub>Start-Up</sub>. Then the Error-Latch is reset by Power Up Reset and the external Soft-Start capacitor C<sub>Soft-Start</sub> is charged by the internal pull-up resistor R<sub>Soft-Start</sub>. During the Soft-Start Phase which ends when the voltage at pin SoftS exceeds 5.3V the detection of overload and open loop by C3 and G2 is inactive. In this way the Start Up Phase is not detected as an overload.





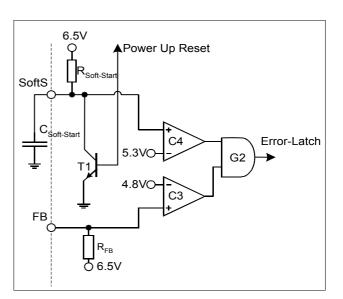


Figure 22 FB-Detection



No Load

3.8.2

## **Functional Description**

But the Soft-Start Phase must be finished within the Start Up Phase to force the voltage at pin FB below the failure detection threshold of 4.8V.

normal operation mode is prevented from overvoltage detection due to varying of VCC concerning the regulation of the converter output. When the voltage V<sub>SoftS</sub> is above 4.0V the overvoltage detection by C1 is deactivated.

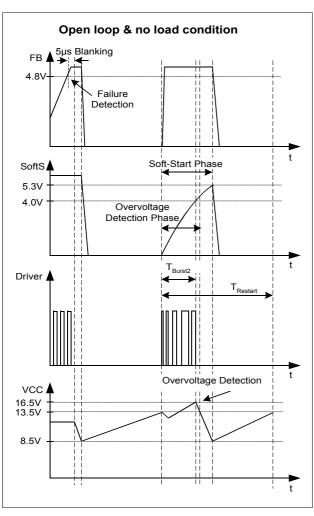


Figure 23 Auto Restart Mode

Figure 23 shows the Auto Restart Mode for open loop and no load condition. In case of this failure mode the converter output voltage increases and also VCC. An additional protection by the comparators C1, C2 and the AND-gate G1 is implemented to consider this failure mode (see Figure 24). The overvoltage detection is provided by Comparator C1 only in the first time during the Soft-Start Phase till the Soft-Start voltage exceeds the threshold of the Comparator C2 at 4.0V and the voltage at pin FB is above 4.8V. When VCC exceeds 16.5V during the overvoltage detection phase C1 can set the Error-Latch and the Burst Phase during Auto Restart Mode is finished earlier. In that case  $T_{\text{Burst2}}$  is shorter than  $T_{\text{Soft-Start}}.$  By means of C2 the

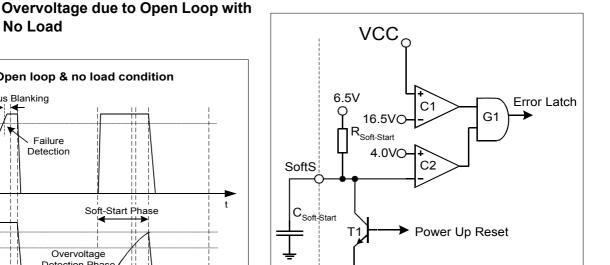


Figure 24 **Overvoltage Detection** 

#### 3.8.3 Thermal Shut Down

Thermal Shut Down is latched by the Error-Latch when junction temperature T<sub>i</sub> of the pwm controller is exceeding an internal threshold of 140°C. In that case the IC switches in Auto Restart Mode.

Note: All the values which are mentioned in the functional description are typical. Please refer to Electrical Characteristics for min/max limit values.



## 4 Electrical Characteristics

#### 4.1 Absolute Maximum Ratings

Note: Absolute maximum ratings are defined as ratings, which when being exceeded may lead to destruction of the integrated circuit. For the same reason make sure, that any capacitor that will be connected to pin 6 (VCC) is discharged before assembling the application circuit.

Parameter	Parameter		Lim	it Values	Unit	Remarks
			min.	max.		
Drain Source Voltage ICE2A0565/165/265/365/765I/765P2 ICE2B0565/165/265/365/765I/765P2 ICE2A0565G ICE2A0565Z		V <sub>DS</sub>	-	650	V	<i>T</i> <sub>j</sub> = 110°C
Drain Source Voltage ICE2A180Z/280Z/380	>2	V <sub>DS</sub>	-	800	V	$T_{\rm j}$ = 25°C
Pulsed drain current, $t_p$ limited by $T_{jmax}$	ICE2A0565/ ICE2B056/ ICE2A0565G/ ICE2A0565Z	I <sub>D_Puls1</sub>		2.0	A	
	ICE2A165/ ICE2B165	I <sub>D_Puls2</sub>		3.8	A	
	ICE2A265/ ICE2B265	I <sub>D_Puls3</sub>		9.8	A	
	ICE2A365/ ICE2B365	I <sub>D_Puls4</sub>		23.3	A	
	ICE2A180Z	I <sub>D_Puls5</sub>		4.1	A	
	ICE2A280Z	I <sub>D_Puls6</sub>		14.8	А	
	ICE2A765P2/ ICE2B765P2/ ICE2A765I/ ICE2B765I	I <sub>D_Puls7</sub>		19.0	A	
	ICE2A380P2/	I <sub>D_Puls8</sub>		5.7	А	



Parameter		Symbol	Limi	t Values	Unit	Remarks
			min.	max.		
Avalanche energy,	ICE2A0565	E <sub>AR1</sub>	-	0.01	mJ	
repetitive $t_{AR}$ limited by max. $T_i = 150^{\circ}C^{1}$	ICE2A165	E <sub>AR2</sub>	-	0.07	mJ	
J	ICE2A265	E <sub>AR3</sub>	-	0.40	mJ	
	ICE2A365	E <sub>AR4</sub>	-	0.50	mJ	
	ICE2B0565	E <sub>AR5</sub>	-	0.01	mJ	
	ICE2B165	E <sub>AR6</sub>	-	0.07	mJ	
	ICE2B265	E <sub>AR7</sub>	-	0.40	mJ	
	ICE2B365	E <sub>AR8</sub>	-	0.50	mJ	
	ICE2A0565G	E <sub>AR9</sub>	-	0.01	mJ	
	ICE2A0565Z	E <sub>AR10</sub>	-	0.01	mJ	
	ICE2A180Z	E <sub>AR11</sub>	-	0.07	mJ	
	ICE2A280Z	E <sub>AR12</sub>	-	0.40	mJ	
	ICE2A765I	E <sub>AR13</sub>	-	0.50	mJ	
	ICE2B765I	E <sub>AR14</sub>	-	0.50	mJ	
	ICE2A765P2	E <sub>AR15</sub>	-	0.50	mJ	
	ICE2B765P2	E <sub>AR16</sub>	-	0.50	mJ	
	ICE2A380P2	E <sub>AR17</sub>	-	0.06	mJ	

<sup>1)</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR}^* f$ 



Parameter		Symbol	Lim	it Values	Unit	Remarks
			min.	max.		
Avalanche current,	ICE2A0565	I <sub>AR1</sub>	-	0.5	А	
repetitive tAR limited by max. <i>T</i> <sub>i</sub> =150°C	ICE2A165	I <sub>AR2</sub>	-	1	А	
	ICE2A265	I <sub>AR3</sub>	-	2	А	
	ICE2A365	I <sub>AR4</sub>	-	3	А	
	ICE2B0565	I <sub>AR5</sub>	-	0.5	А	
	ICE2B165	I <sub>AR6</sub>	-	1	А	
	ICE2B265	I <sub>AR7</sub>	-	2	А	
	ICE2B365	I <sub>AR8</sub>	-	3	А	
	ICE2A0565G	I <sub>AR9</sub>	-	0.5	А	
	ICE2A0565Z	I <sub>AR10</sub>	-	0.5	А	
	ICE2A180Z	I <sub>AR11</sub>	-	1	А	
	ICE2A280Z	I <sub>AR12</sub>	-	2	А	
	ICE2A765I	I <sub>AR13</sub>	-	7	А	
	ICE2B765I	I <sub>AR14</sub>	-	7	А	
	ICE2A765P2	I <sub>AR15</sub>	-	7	А	
	ICE2B765P2	I <sub>AR16</sub>	-	7	А	
	ICE2A380P2	I <sub>AR17</sub>	-	2.4	А	
V <sub>CC</sub> Supply Voltage		V <sub>cc</sub>	-0.3	22	V	
FB Voltage		V <sub>FB</sub>	-0.3	6.5	V	
SoftS Voltage		V <sub>SoftS</sub>	-0.3	6.5	V	
Sense		I <sub>Sense</sub>	-0.3	3	V	
Junction Temperature		Tj	-40	150	°C	Controller & CoolMOS™
Storage Temperature		Ts	-50	150	°C	
Thermal Resistance		R <sub>thJA1</sub>	-	90	K/W	PG-DIP-8-6
Junction-Ambient		R <sub>thJA2</sub>	-	96	K/W	PG-DIP-7-1
		R <sub>thJA3</sub>	-	110	K/W	P-DSO-16/12
ESD Robustness <sup>1)</sup>		V <sub>ESD</sub>	-	2 <sup>2)</sup>	kV	Human Body Model

 $^{1)}\,$  Equivalent to discharging a 100pF capacitor through a 1.5 k $\Omega$  series resistor

 $^{\rm 2)}~$  1kV at pin drain of ICE2x0565, ICE2A0565Z and ICE2A0565G



### 4.2 Thermal Impedance (ICE2X765I and ICE2X765P2)

Parameter		Symbol	Limit Values		Unit	Remarks	
			min.	max.			
Thermal Resistance Junction-Ambient	ICE2A765I ICE2B765I ICE2A765P2 ICE2B765P2	R <sub>thJA4</sub>	-	74	K/W	Free standing with no heat-sink	
	ICE2A380P2	R <sub>thJA5</sub>	-	82	K/W		
Junction-Case	ICE2A765I ICE2B765I ICE2A765P2 ICE2B765P2	R <sub>thJC1</sub>	-	2.5	K/W		
	ICE2A380P2	R <sub>thJC2</sub>	-	2.86	K/W		

### 4.3 Operating Range

Note: Within the operating range the IC operates as described in the functional description.

Parameter	Symbol	Symbol Limit V		Unit	Remarks		
		min.	max.				
V <sub>CC</sub> Supply Voltage	V <sub>CC</sub>	V <sub>CCoff</sub>	21	V			
Junction Temperature of Controller	T <sub>JCon</sub>	-25	130	°C	Limited due to thermal shut down of controller		
Junction Temperature of CoolMOS™	T <sub>JCoolMOS</sub>	-25	150	°C			



#### 4.4 Characteristics

Note: The electrical characteristics involve the spread of values given within the specified supply voltage and junction temperature range  $T_J$  from – 25 °C to 125 °C. Typical values represent the median values, which are related to 25 °C. If not otherwise stated, a supply voltage of  $V_{CC}$  = 15 V is assumed.

#### 4.4.1 Supply Section

Parameter		Symbol		Limit Val	ues	Unit	Test Condition
			min.	typ.	max.		
Start Up Current		I <sub>VCC1</sub>	-	27	55	μA	V <sub>CC</sub> =V <sub>CCon</sub> -0.1V
Supply Current w Gate	ith Inactive	I <sub>VCC2</sub>	-	5.0	6.6	mA	$V_{\text{SoftS}} = 0$ $I_{\text{FB}} = 0$
Supply Current	ICE2A0565	I <sub>VCC3</sub>	-	5.3	6.7	mA	V <sub>SoftS</sub> = 5V
with Active Gate	ICE2A165	I <sub>VCC4</sub>	-	6.5	7.8	mA	/ <sub>FB</sub> = 0
	ICE2A265	I <sub>VCC5</sub>	-	6.7	8.0	mA	
	ICE2A365	I <sub>VCC6</sub>	-	8.5	9.8	mA	
	ICE2B0565	I <sub>VCC7</sub>	-	5.2	6.7	mA	
	ICE2B165	I <sub>VCC8</sub>	-	5.5	7.0	mA	
	ICE2B265	I <sub>VCC9</sub>	-	6.1	7.3	mA	
	ICE2B365	I <sub>VCC10</sub>	-	7.1	8.3	mA	
	ICE2A0565G	I <sub>VCC11</sub>	-	5.3	6.7	mA	
	ICE2A0565Z	I <sub>VCC12</sub>	-	5.3	6.7	mA	
	ICE2A180Z	I <sub>VCC13</sub>	-	6.5	7.8	mA	
	ICE2A280Z	I <sub>VCC14</sub>	-	7.7	9.0	mA	
Supply Current	ICE2A765I	I <sub>VCC15</sub>	-	8.5	9.8	mA	$V_{\text{Softs}} = 5V$
with Active Gate	ICE2B765I	I <sub>VCC16</sub>	-	7.1	8.3	mA	/ <sub>FB</sub> = 0
	ICE2A765P2	I <sub>VCC17</sub>	-	8.5	9.8	mA	
	ICE2B765P2	I <sub>VCC18</sub>	-	7.1	8.3	mA	
	ICE2A380P2	I <sub>VCC19</sub>	-	6.7	8.0	mA	
VCC Turn-On Threshold VCC Turn-Off Threshold VCC Turn-On/Off Hysteresis		V <sub>CCon</sub> V <sub>CCoff</sub> V <sub>CCHY</sub>	13 - 4.5	13.5 8.5 5	14 - 5.5	V V V	



## 4.4.2 Internal Voltage Reference

Parameter	Symbol	Limit Values		Limit Values		Unit	Test Condition
		min.	typ.	max.			
Trimmed Reference Voltage	V <sub>REF</sub>	6.37	6.50	6.63	V	measured at pin FB	

#### 4.4.3 Control Section

Parameter	Symbol	Limit Values			Unit	Test Condition
		min.	typ.	max.		
Oscillator Frequency ICE2A0565/165/265/365/765I/765P2 ICE2A0565G/0565Z/180Z/280Z/380P2	f <sub>OSC1</sub>	93	100	107	kHz	V <sub>FB</sub> = 4V
Oscillator Frequency ICE2B0565/165/265/365/765I/765P2	f <sub>OSC3</sub>	62	67	72	kHz	V <sub>FB</sub> = 4V
Reduced Osc. Frequency ICE2A0565/165/265/365/765I/765P2 ICE2A0565G/0565Z/180Z/280Z/380P2	f <sub>OSC2</sub>	-	21.5	-	kHz	V <sub>FB</sub> = 1V
Reduced Osc. Frequency ICE2B0565/165/265/365/765I/765P2	f <sub>OSC4</sub>	-	20	-	kHz	V <sub>FB</sub> = 1V
Frequency Ratio <i>f</i> <sub>osc1</sub> / <i>f</i> <sub>osc2</sub> ICE2A0565/165/265/365/765I/765P2 ICE2A0565G/0565Z/180Z/280Z/380P2		4.5	4.65	4.9		
Frequency Ratio <i>f</i> <sub>osc3</sub> / <i>f</i> <sub>osc4</sub> ICE2B0565/165/265/365/765I/765P2		3.18	3.35	3.53		
Max Duty Cycle	D <sub>max</sub>	0.67	0.72	0.77		
Min Duty Cycle	D <sub>min</sub>	0	-	-		V <sub>FB</sub> < 0.3V
PWM-OP Gain	$A_{ m v}$	3.45	3.65	3.85		
V <sub>FB</sub> Operating Range Min Level	V <sub>FBmin</sub>	0.3	-	-	V	
V <sub>FB</sub> Operating Range Max level	V <sub>FBmax</sub>	-	-	4.6	V	
Feedback Resistance	R <sub>FB</sub>	3.0	3.7	4.9	kΩ	
Soft-Start Resistance	R <sub>Soft-Start</sub>	42	50	62	kΩ	



### 4.4.4 **Protection Unit**

Parameter	Symbol		Limit Val	ues	Unit	<b>Test Condition</b>
		min.	typ.	max.		
Over Load & Open Loop Detection Limit	V <sub>FB2</sub>	4.65	4.8	4.95	V	V <sub>SoftS</sub> > 5.5V
Activation Limit of Overload & Open Loop Detection	V <sub>SoftS1</sub>	5.15	5.3	5.46	V	V <sub>FB</sub> > 5V
Deactivation Limit of Overvoltage Detection	V <sub>SoftS2</sub>	3.88	4.0	4.12	V	V <sub>FB</sub> > 5V V <sub>CC</sub> > 17.5V
Overvoltage Detection Limit	V <sub>VCC1</sub>	16	16.5	17.2	V	$V_{SoftS} < 3.8V$ $V_{FB} > 5V$
Latched Thermal Shutdown	T <sub>jSD</sub>	130	140	150	°C	1)
Spike Blanking	t <sub>Spike</sub>	-	5	-	μs	

<sup>1)</sup> The parameter is not subject to production test - verified by design/characterization

## 4.4.5 Current Limiting

Parameter	ter Symbol		.imit Valu	es	Unit	Test Condition	
		min.	typ.	max.			
Peak Current Limitation (incl. Propagation Delay Time)	V <sub>csth</sub>	0.95	1.0	1.05	V	$dV_{sense}/dt = 0.6V/\mu s$	
Leading Edge Blanking	t <sub>LEB</sub>	-	220	-	ns		



#### 4.4.6 CoolMOS<sup>™</sup> Section

Parameter		Symbol		Limit Val	ues	Unit	Test Condition
			min.	typ. max			
Drain Source Breakdown Voltage ICE2A0565/165/265/365/765I/765P2 ICE2B0565/165/265/365/765I/765P2 ICE2A0565G/0565Z		V <sub>(BR)DSS</sub>	600 650	-	-	V V	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =110°C
Drain Source Bre ICE2A180Z/280Z		V <sub>(BR)DSS</sub>	800 870	-		V V	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =110°C
Drain Source On-Resistance	ICE2A0565	R <sub>DSon1</sub>		4.7 10.0	5.5 12.5	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2A165	R <sub>DSon2</sub>		3 6.6	3.3 7.3	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2A265	R <sub>DSon3</sub>		0.9 1.9	1.08 2.28	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2A365	R <sub>DSon4</sub>		0.45 0.95	0.54 1.14	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2B0565	R <sub>DSon5</sub>		4.7 10.0	5.5 12.5	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2B165	R <sub>DSon6</sub>		3 6.6	3.3 7.3	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2B265	R <sub>DSon7</sub>		0.9 1.9	1.08 2.28	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2B365	R <sub>DSon8</sub>		0.45 0.95	0.54 1.14	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2A0565G	R <sub>DSon9</sub>		4.7 10.0	5.5 12.5	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2A0565Z	R <sub>DSon10</sub>		4.7 10.0	5.5 12.5	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2A180Z	R <sub>DSon11</sub>		3 6.6	3.3 7.3	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2A280Z	R <sub>DSon12</sub>		0.8 1.7	1.06 2.04	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2A765I	R <sub>DSon13</sub>		0.45 0.95	0.54 1.14	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>j</sub> =125°C
	ICE2B765I	R <sub>DSon14</sub>		0.45 0.95	0.54 1.14	Ω Ω	$T_j=25^{\circ}C$ $T_j=125^{\circ}C$
	ICE2A765P2	R <sub>DSon15</sub>		0.45 0.95	0.54 1.14	Ω Ω	$T_j=25^{\circ}C$ $T_j=125^{\circ}C$
	ICE2B765P2	R <sub>DSon16</sub>		0.45 0.95	0.54 1.14	Ω Ω	$T_j=25^{\circ}C$ $T_j=125^{\circ}C$
	ICE2A380P2	R <sub>DSon17</sub>		1.89 4.15	2.27 4.98	Ω Ω	<i>T</i> <sub>j</sub> =25°C <i>T</i> <sub>i</sub> =125°C



Parameter		Symbol		Limit Valu	ues	Unit	<b>Test Condition</b>
			min.	typ.	max.		
Effective output	ICE2A0565	C <sub>o(er)1</sub>	-	4.751	-	pF	V <sub>DS</sub> =0V to 480V
capacitance, energy related	ICE2A165	C <sub>o(er)2</sub>	-	7	-	pF	
5, 111	ICE2A265	C <sub>o(er)3</sub>	-	21	-	pF	
	ICE2A365	C <sub>o(er)4</sub>	-	30	-	pF	
	ICE2B0565	C <sub>o(er)5</sub>	-	4.751	-	pF	
	ICE2B165	C <sub>o(er)6</sub>	-	7	-	pF	
	ICE2B265	C <sub>o(er)7</sub>	-	21	-	pF	
	ICE2B365	C <sub>o(er)8</sub>	-	30	-	pF	
	ICE2A0565G	C <sub>o(er)9</sub>	-	4.751	-	pF	
	ICE2A0565Z	C <sub>o(er)10</sub>	-	4.751	-	pF	
	ICE2A180Z	C <sub>o(er)11</sub>	-	7	-	pF	
	ICE2A280Z	C <sub>o(er)12</sub>	-	22	-	pF	
	ICE2A765I	C <sub>o(er)13</sub>	-	30	-	pF	
	ICE2B765I	C <sub>o(er)14</sub>	-	30	-	pF	
	ICE2A765P2	C <sub>o(er)15</sub>	-	30	-	pF	
	ICE2B765P2	C <sub>o(er)16</sub>	-	30	-	pF	
	ICE2A380P2	C <sub>o(er)17</sub>	-	16.8	-	pF	
Zero Gate Voltage	e Drain Current	I <sub>DSS</sub>	-	0.5	-	μA	V <sub>VCC</sub> =0V
Rise Time		<i>t</i> <sub>rise</sub>	-	30 <sup>1)</sup>	-	ns	
Fall Time		t <sub>fall</sub>	-	30 <sup>1)</sup>	-	ns	

<sup>1)</sup> Measured in a Typical Flyback Converter Application



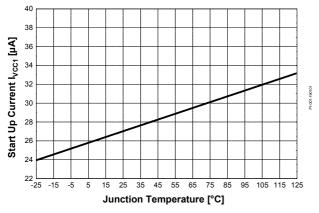
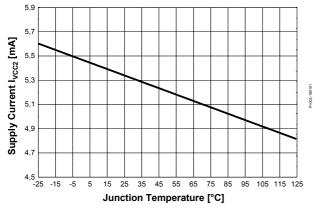
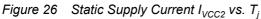
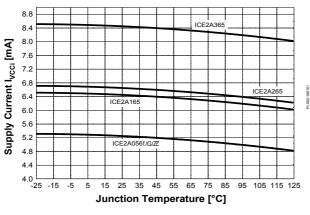
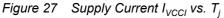


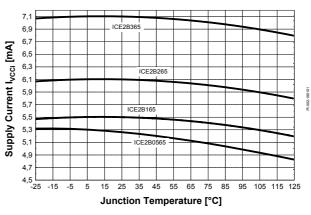
Figure 25 Start Up Current  $I_{VCC1}$  vs.  $T_j$ 

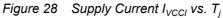


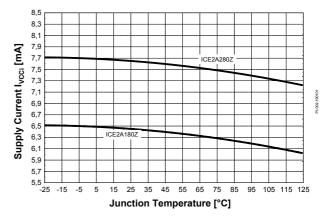


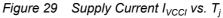












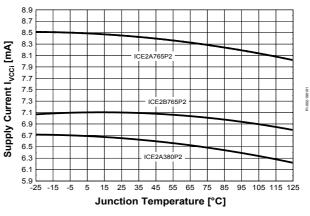


Figure 30 Supply Current  $I_{VCCI}$  vs.  $T_j$ 



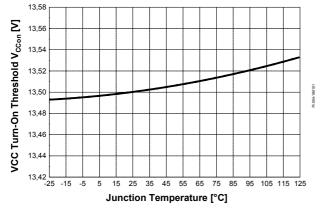


Figure 31 VCC Turn-On Threshold V<sub>CCon</sub> vs. T<sub>j</sub>

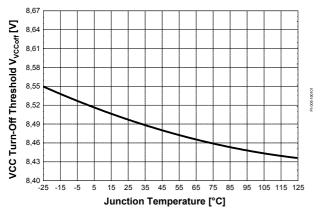


Figure 32 VCC Turn-Off Threshold V<sub>VCCoff</sub> vs. T<sub>j</sub>

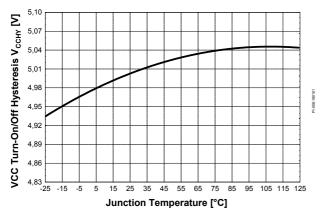


Figure 33 VCC Turn-On/Off Hysteresis V<sub>VCCHY</sub> vs. T<sub>j</sub>

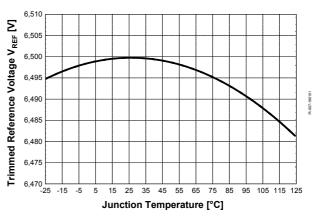


Figure 34 Trimmed Reference  $V_{REF}$  vs.  $T_j$ 

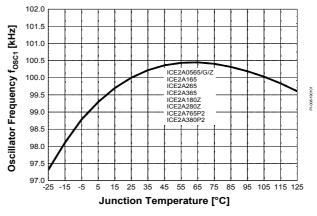


Figure 35 Oscillator Frequency  $f_{OSC1}$  vs.  $T_i$ 

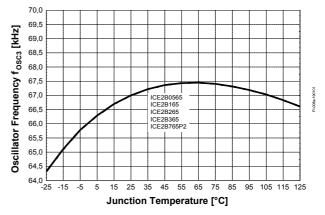


Figure 36 Oscillator Frequency  $f_{OSC3}$  vs.  $T_j$ 



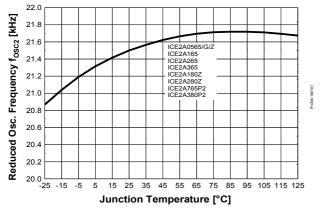


Figure 37 Reduced Osc. Frequency f<sub>OSC2</sub> vs. T<sub>i</sub>

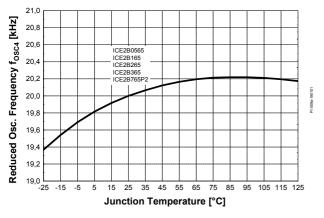


Figure 38 Reduced Osc. Frequency f<sub>OSC4</sub> vs. T<sub>j</sub>

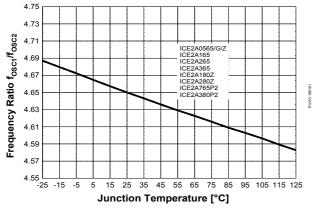


Figure 39 Frequency Ratio  $f_{OSC1} / f_{OSC2}$  vs.  $T_j$ 

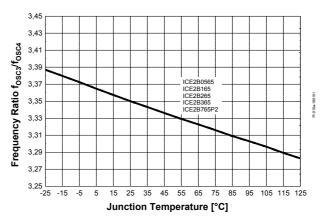


Figure 40 Frequency Ratio  $f_{OSC3} / f_{OSC4}$  vs.  $T_j$ 

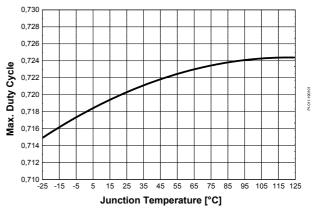


Figure 41 Max. Duty Cycle vs. T<sub>j</sub>

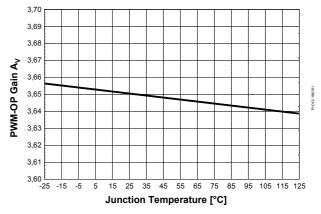


Figure 42 PWM-OP Gain  $A_V$  vs.  $T_j$ 



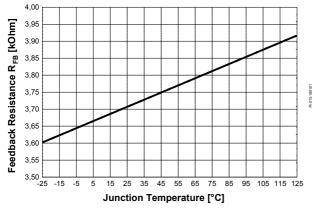


Figure 43 Feedback Resistance R<sub>FB</sub> vs. T<sub>i</sub>

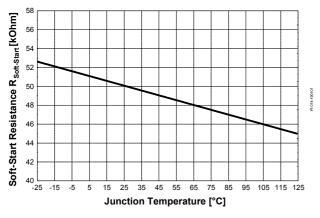
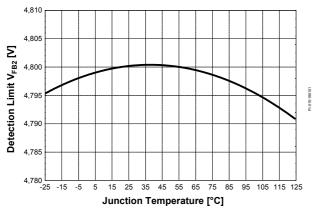
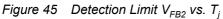


Figure 44 Soft-Start Resistance R<sub>Soft-Start</sub> vs. T<sub>j</sub>





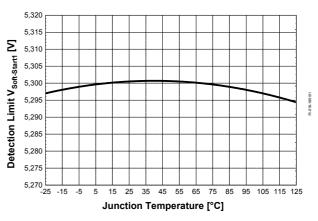


Figure 46 Detection Limit  $V_{Soft-Start1}$  vs.  $T_j$ 

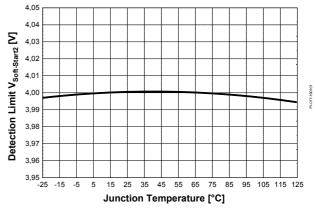


Figure 47 Detection Limit V<sub>Soft-Start2</sub> vs. T<sub>j</sub>

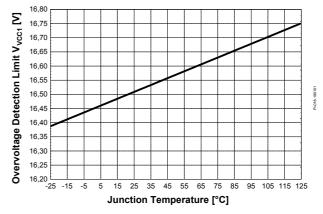


Figure 48 Overvoltage Detection Limit  $V_{VCC1}$  vs.  $T_j$ 



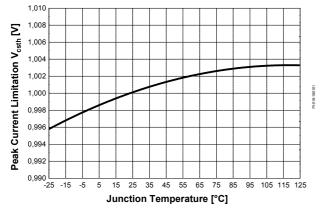


Figure 49 Peak Current Limitation V<sub>csth</sub> vs. T<sub>j</sub>

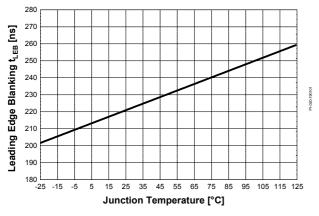


Figure 50 Leading Edge Blanking  $V_{VCC1}$  vs.  $T_j$ 

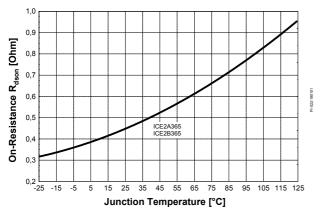


Figure 51 Drain Source On-Resistance R<sub>DSon</sub> vs. T<sub>j</sub>

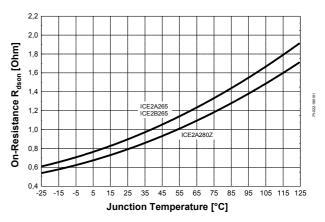


Figure 52 Drain Source On-Resistance R<sub>DSon</sub> vs. T<sub>i</sub>

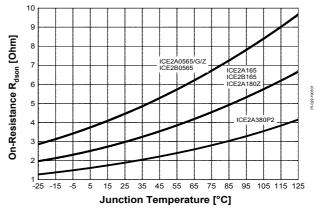


Figure 53 Drain Source On-Resistance R<sub>DSon</sub> vs. T<sub>j</sub>

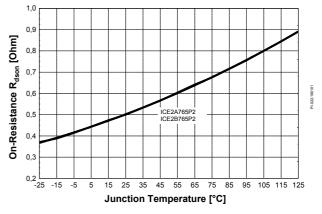


Figure 54 Drain Source On-Resistance R<sub>DSon</sub> vs. T<sub>i</sub>



## CoolSET<sup>™</sup>-F2

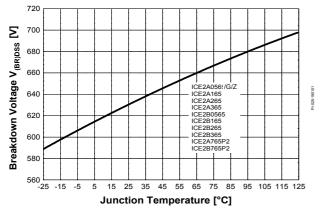


Figure 55 Breakdown Voltage V<sub>BR(DSS)</sub> vs. T<sub>i</sub>

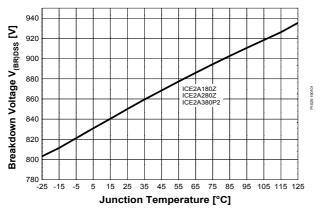


Figure 56 Breakdown Voltage V<sub>BR(DSS)</sub> vs. T<sub>j</sub>



## Layout Recommendation for $C_{18}$

## 6 Layout Recommendation for C<sub>18</sub>

Note: Only for ICE2A765I/P2 and ICE2B765I/P2

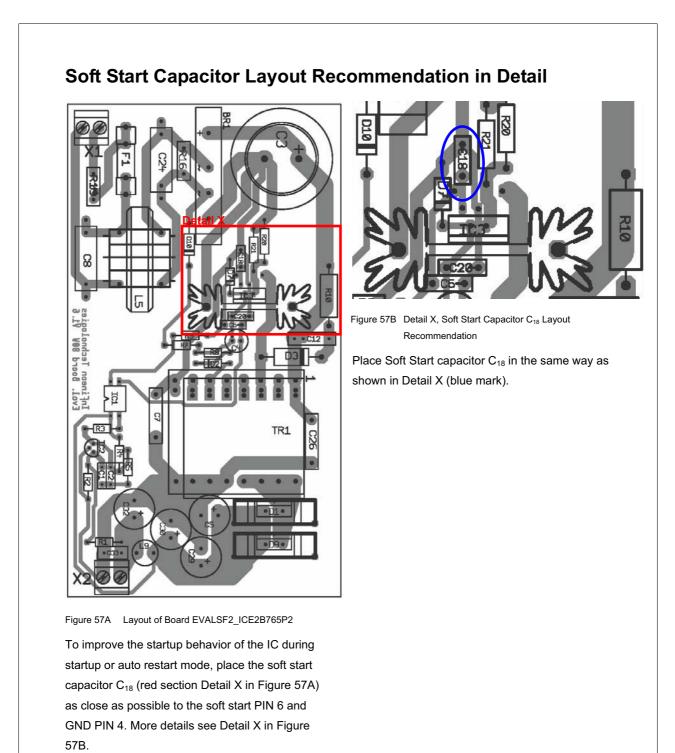


Figure 57 Layout Recommendation for ICE2A765I/P2 and ICE2B765I/P2



## **Outline Dimension**

## 7 Outline Dimension

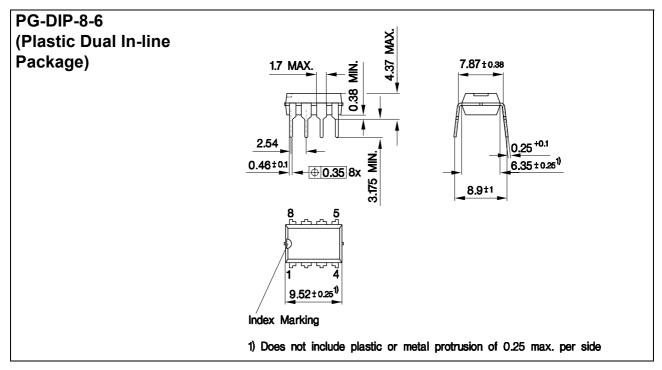


Figure 58 PG-DIP-8-6 (Plastic Dual In-line Package)

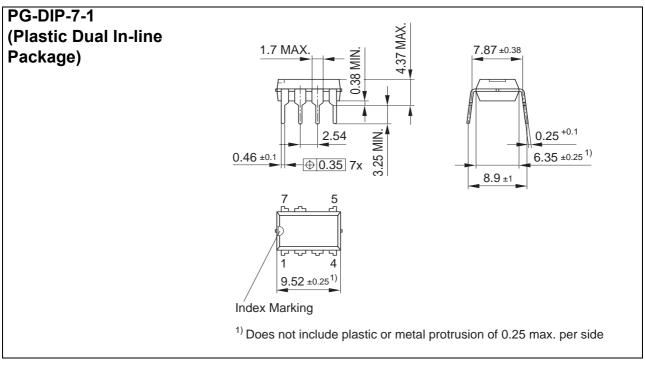


Figure 59 PG-DIP-7-1 (Plastic Dual In-line Package)

Dimensions in mm



## **Outline Dimension**

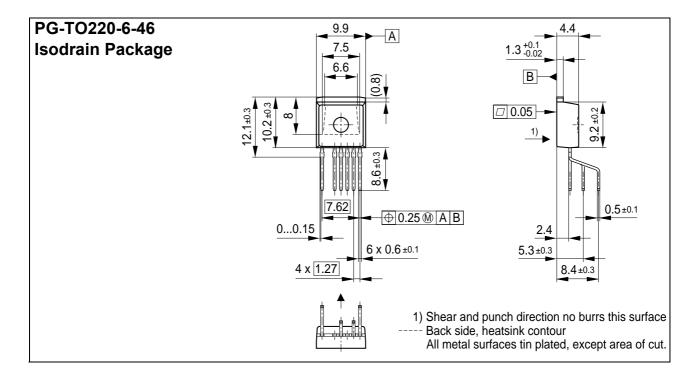


Figure 60 PG-TO220-6-46 (Isodrain Package)

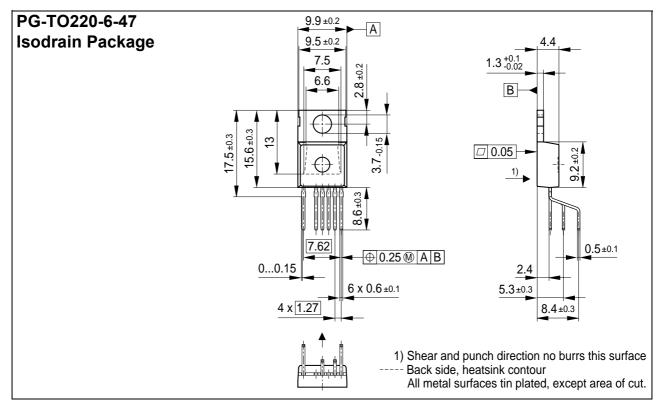


Figure 61 PG-TO220-6-47 (Isodrain Package)

Dimensions in mm



## **Outline Dimension**

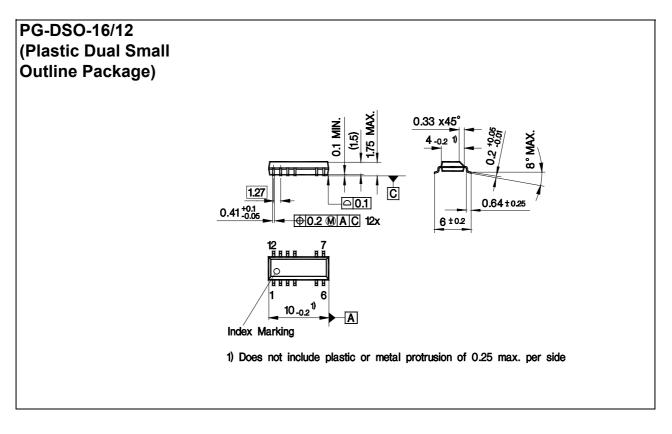


Figure 62 PG-DSO-16/12 (Plastic Dual Small Outline Package)

Dimensions in mm

## Total Quality Management

Qualität hat für uns eine umfassende Bedeutung. Wir wollen allen Ihren Ansprüchen in der bestmöglichen Weise gerecht werden. Es geht uns also nicht nur um die Produktqualität – unsere Anstrengungen gelten gleichermaßen der Lieferqualität und Logistik, dem Service und Support sowie allen sonstigen Beratungs- und Betreuungsleistungen.

Dazu gehört eine bestimmte Geisteshaltung unserer Mitarbeiter. Total Quality im Denken und Handeln gegenüber Kollegen, Lieferanten und Ihnen, unserem Kunden. Unsere Leitlinie ist jede Aufgabe mit "Null Fehlern" zu lösen – in offener Sichtweise auch über den eigenen Arbeitsplatz hinaus – und uns ständig zu verbessern.

Unternehmensweit orientieren wir uns dabei auch an "top" (Time Optimized Processes), um Ihnen durch größere Schnelligkeit den entscheidenden Wettbewerbsvorsprung zu verschaffen.

Geben Sie uns die Chance, hohe Leistung durch umfassende Qualität zu beweisen.

Wir werden Sie überzeugen.

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Part of this is the very special attitude of our staff. Total Quality in thought and deed, towards co-workers, suppliers and you, our customer. Our guideline is "do everything with zero defects", in an open manner that is demonstrated beyond your immediate workplace, and to constantly improve.

Throughout the corporation we also think in terms of Time Optimized Processes (top), greater speed on our part to give you that decisive competitive edge.

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